

ABSTRACT

The present invention relates to a semiconductor memory device in which information is written into a storage element by flowing current. The invention aims at shortening write speed and reducing power consumption by preventing parasitic capacitors from prolonging the time required for a write current to reach a predetermined value. The apparatus includes storage elements for storing information, a constant current [[103]] source for writing information into the storage element by flowing current, and a boost [[101]] circuit for charging parasitic capacitors by a time when an amount of a current flowed by said constant current source reaches an amount of a current required to write information into the storage element, at a predetermined position related to the storage element.